

**Amendments to the Claims:**

The following listing of claims will replace all prior versions, and listings, of claims in the application:

Please cancel claims 1-4.

5. (New) A method for producing a silicon wafer having a crystal orientation <110> from a silicon single crystal ingot grown by Floating Zone method (FZ method), wherein, at least, an FZ silicon single crystal ingot is grown by being made to be dislocation-free by Dash Necking method using a seed crystal having its crystal axis inclined at a specified angle from a crystal orientation <110>, and the grown FZ silicon single crystal ingot is sliced at the just angle of a crystal orientation <110> to produce a silicon wafer having a crystal orientation <110>.

6. (New) The method for producing a silicon wafer according to Claim 5, wherein the sliced silicon wafer having a crystal orientation <110> is made to be a perfect circle by processing of chamfering.

7. (New) The method for producing a silicon wafer according to Claim 5, wherein the specified angle of inclining the seed crystal is 1° to 30°.

8. (New) The method for producing a silicon wafer according to Claim 6, wherein the specified angle of inclining the seed crystal is 1° to 30°.

9. (New) The silicon wafer having a crystal orientation <110> produced by the method of producing a silicon wafer according to Claim 5.

10. (New) The silicon wafer having a crystal orientation <110> produced by the method of producing a silicon wafer according to Claim 6.

11. (New) The silicon wafer having a crystal orientation <110> produced by the method of producing a silicon wafer according to Claim 7.

12. (New) The silicon wafer having a crystal orientation <110> produced by the method of producing a silicon wafer according to Claim 8.